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TFF1007HN

Low phase noise LO generator for VSAT applications

Rev. 1 — 23 August 2012

Product data sheet

1. General description

The TFF1007HN is a frequency generator intended for low phase noise Local Oscillator (LO) circuits for K_a band VSAT transmitters and transceivers. The specified phase noise complies with IESS-308 from Intelsat.

2. Features and benefits

- Phase noise compliant with IESS-308 (Intelsat)
- LO generator with VCO range from 14.62 GHz to 15.00 GHz
- Input signal 228.44 MHz to 234.38 MHz
- Divider setting 64
- Output level –4 dBm minimum
- Third or fourth order PLL
- Internally stabilized voltage reference for loop filter

3. Applications

- VSAT up converters
- Local oscillator signal generation

4. Quick reference data

Table 1. Quick reference data

 $T_{case} = 25$ °C.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		3.0	3.3	3.6	V
I _{CC}	supply current		-	116	130	mA
f _{o(RF)}	RF output frequency	in locked state	14.62	-	15.00	GHz
$\phi_{\text{n(synth)}}$	synthesizer phase noise	divider value = 64 with loop bandwidth = 2 MHz; reference phase noise = -150 dBc/Hz; at 100 kHz offset	-	-109	-104	dBc/Hz
RL _{out}	output return loss	measured at demo board and de-embedded to footprint	-	-10	-	dB



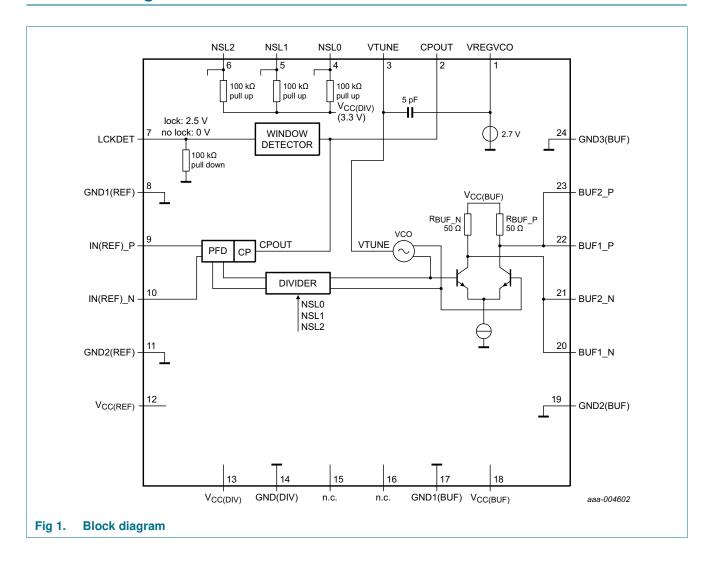
Low phase noise LO generator for VSAT applications

5. Ordering information

Table 2. Ordering information

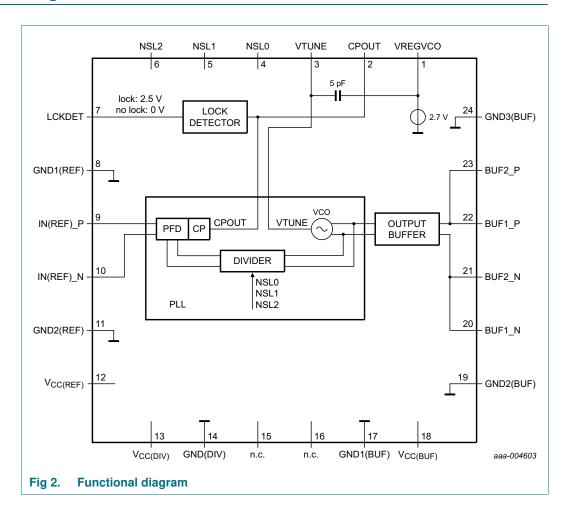
Type number	Package						
	Name	Description	Version				
TFF1007HN	HVQFN24	plastic thermal enhanced very thin quad flat package; no leads; 24 terminals; body $4\times4\times0.85$ mm	SOT616-1				

6. Block diagram



Low phase noise LO generator for VSAT applications

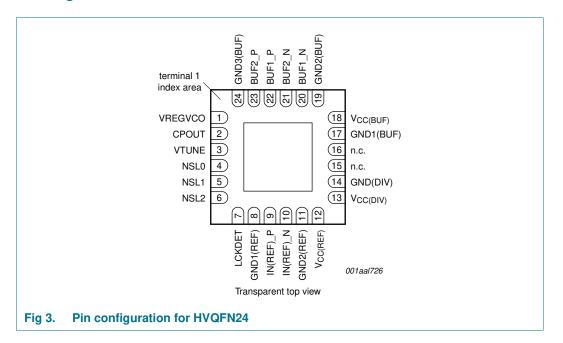
7. Functional diagram



Low phase noise LO generator for VSAT applications

8. Pinning information

8.1 Pinning



8.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
VREGVCO	1	Regulated output voltage for VCO loop filter. Connect loop filter to this pin.
CPOUT	2	Charge pump output.
VTUNE	3	Tuning voltage for VCO.
NSL0	4	Divider setting, LSB. Leave open for "1", connect to GND for "0". See Table 6.
NSL1	5	Divider setting. Leave open for "1", connect to GND for "0". See Table 6.
NSL2	6	Divider setting, MSB. Leave open for "1", connect to GND for "0". See <u>Table 6</u> .
LCKDET	7	Lock detect. Lock = 2.5 V; out of lock = 0 V. See <u>Table 4</u> .
GND1(REF)	8	Ground for REF input. Connect this pin to the exposed diepad landing.
IN(REF)_P	9	Reference signal, non-inverting input. Couple this AC to the source.
IN(REF)_N	10	Reference signal, inverting input. Couple this AC to the source.
GND2(REF)	11	Ground for REF input. Connect this pin to the exposed diepad landing.
$V_{\text{CC}(\text{REF})}$	12	Supply of the internal regulated voltages. Decouple this pin against GND2(REF) (pin 11).
$V_{CC(DIV)}$	13	Supply of the divider and PFD/CP. Decouple this pin against GND(DIV) (pin 14).
GND(DIV)	14	Ground of the divider. Connect this pin to the exposed diepad landing.
n.c.	15	not connected
n.c.	16	not connected
GND1(BUF)	17	Ground for RF output. Connect this pin to the exposed diepad landing.

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Table 3. Pin description ... continued

Symbol	Pin	Description
V _{CC(BUF)}	18	Supply voltage for the RF output buffer. Decouple this pin against GND2(BUF) (pin 19).
GND2(BUF)	19	Ground for RF output. Connect this pin to the exposed diepad landing.
BUF1_N	20	RF output.
BUF2_N	21	RF output.
BUF1_P	22	RF output.
BUF2_P	23	RF output.
GND3(BUF)	24	Ground for RF output. Connect this pin to the exposed diepad landing.

9. Functional description

The TFF1007HN consists of the following blocks:

- PLL
- · Output buffer
- · Lock detector
- · Reference input
- · Divider settings

The functionality of the blocks will be discussed below.

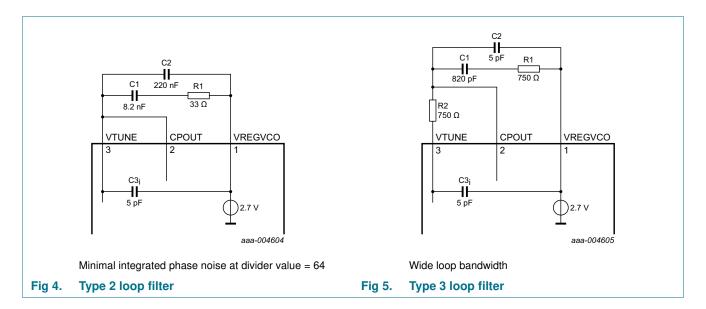
9.1 PLL

The PLL is formed by the VCO, DIVIDER (possible settings: 16, 32, 64, 128 and 256 (see <u>Table 6</u>)) and a PFD/CP. The tune voltage is referred to the band gap regulated voltage: VREGVCO (pin 1).

The loop filter can be set to type 2 or type 3. If a type 2 filter is used, the pins CPOUT (pin 2) and VTUNE (pin 3) must be interconnected. No capacitor is placed internally between CPOUT (pin 2) and VREGVCO (pin 1), and a 5 pF capacitor is placed between VTUNE (pin 3) and VREGVCO (pin 1). See Figure 5. Type 3 filter has an extra pole formed by R2, leading to better spurious suppression.

The VCO input voltage range is between $0.1 \times V_{O(reg)VCO}$ and $0.9 \times V_{O(reg)VCO}$.

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9.2 Output buffer

The output consists of a differential pair with 50 Ω collector resistors. If only one output is used, terminate the non used output with the same impedance as the load (see Figure 8)

9.3 Lock detector

The lock detector is the output of a window detector. The window detector compares the output voltage over the charge pump. This voltage is identical to VTUNE (pin 3) when a type 2 loop filter is used (see <u>Figure 4</u>). In case of a type 3 loop filter this voltage is filtered by R2/C3 (see <u>Figure 5</u>). Due to this filtering the attack and decay time will decrease.

The lower window detector threshold voltage is 7 % of the output voltage on pin VREGVCO (pin 1), the upper window detector threshold voltage is 93 % of the output voltage on pin VREGVCO (pin 1). The hysteresis is 0.1 V. The output is 2.5 V CMOS compliant. The values are shown in Table 4. The timing diagram is shown in Figure 6.

At start-up the LCKDET (pin 7) will be low until the circuit has acquired lock.

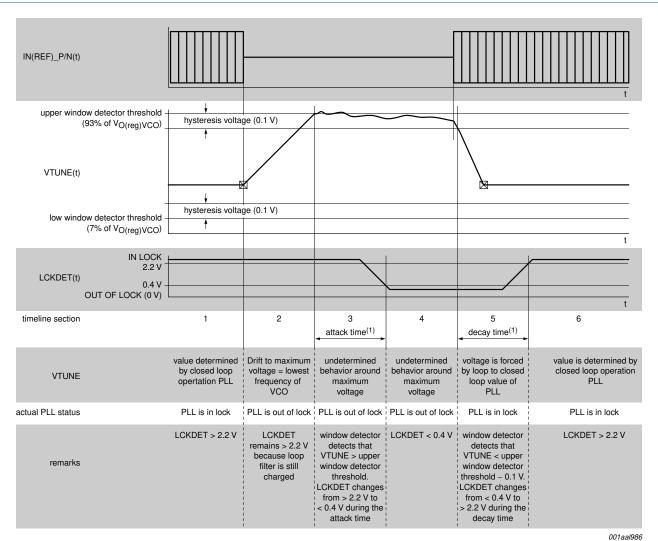
Table 4. Logical value and physical value for lock detect (LCKDET)

Logical value	Physical value	Lock detect state
0	0 V	out of lock
1	2.5 V	lock

LCKDET (pin 7) has a pull-down resistor of 100 k Ω to GND1(REF) (pin 8).

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(1) The attack time and decay time are typically 10 µs and are mainly depending on the drift of the VCO tuning voltage.

Fig 6. Timing diagram lock detector

9.4 Reference input (IN(REF) P, IN(REF) N)

The reference input is a differential pair and is internally biased. The input is high ohmic. The input signal must be AC coupled. If used in a single ended mode, the not used input must be terminated with the same impedance as the driving source.

An example of the differential source and two single ended loads are shown in Figure 7. An example of a single ended application is shown in Figure 8.

Note that the phase noise of the output signal is also determined by the phase noise of the reference signal. The reference frequency range is equal to the output frequency / division value. Note that the output frequency is guaranteed from 14.62 GHz to 15.00 GHz.

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9.5 Divider setting (NSL2, NSL1, NSL0)

The divider is optimized for divider value 64. The other values (16, 32, 128 and 256) can be used, but performance for these values is not included in this data sheet (see <u>Table 6</u>). The logic levels for NSL0 (pin 4), NSL1 (pin 5) and NSL2 (pin 6) are given in <u>Table 5</u>.

The pins have a pull-up resistor of 100 k Ω to $V_{CC(DIV)}$ (pin 13).

The device is only guaranteed when NSL2, NSL1 and NSL0 are predefined at start-up (no change of divider value is allowed during operation).

Table 5. Logical and physical value for divider setting (NSL2, NSL1, NSL0)

Logical value	Physical value
0	GND
1	open or V _{CC}

The truth table is shown in Table 6.

Table 6. Divider setting as function of NSL2, NSL1 and NSL0

Setting number	NSL2	NSL1	NSL0	Divider value
0	0	0	0	16 [<u>1]</u>
1	0	0	1	32 <u>[1]</u>
2	0	1	0	64
3	0	1	1	128 [1]
4	1	0	0	256 ^[1]
5	1	0	1	[2]
6	1	1	0	[2]
7	1	1	1	[2]

^[1] Test mode.

10. Limiting values

Table 7. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _I	input voltage	on pin NSL0	-0.5	+5	V
		on pin NSL1	-0.5	+5	٧
		on pin NSL2	-0.5	+5	٧
		on pin IN(REF)_P	-0.5	+5	٧
		on pin IN(REF)_N	-0.5	+5	٧
		on pin V _{CC(REF)}	-0.5	+5	٧
		on pin V _{CC(DIV)}	-0.5	+5	٧
		on pin V _{CC(BUF)}	-0.5	+5	٧
Pi	input power	on pin IN(REF)_P	-4	+10	dBm
		on pin IN(REF)_N	-4	+10	dBm
Tj	junction temperature		-40	+125	°C

^[2] Test mode, divider output will be disabled.

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 Table 7.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
T _{stg}	storage temperature		-40	+125	°C
V _{ESD}	electrostatic discharge voltage	Human Body Model (HBM); According JEDEC standard 22-A114E	-	2.5	kV
		Charged Device Model (CDM); According to JEDEC standard 22-C101B	-	1	kV

11. Recommended operating conditions

Table 8. Operating conditions

NSL0 (pin 4), NSL1 (pin 5) and NSL2 (Pin 6) not changed during operation.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
T_{amb}	ambient temperature			-40	+25	+85	°C
Z_0	characteristic impedance			-	50	-	Ω
Φn(ref)	reference phase noise	divider value = 64	[1]	-	-	-150	dBc/Hz
f _{i(ref)}	reference input frequency	$f_{i(ref)} = f_{o(RF)} / divider value$		228.44	-	234.38	MHz
P _{i(ref)}	reference input power			-4	-	+4	dBm

^[1] Required reference phase noise is set 10 dB below equivalent input phase noise.

12. Thermal characteristics

Table 9.	Thermal	charact	teristics
Table 3.	HILCHIIIAI	Cilaiac	101131103

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		25	K/W

13. Characteristics

Table 10. Characteristics

 $3.0 < V_{CC} < 3.6 V$; Operating conditions of Table 8 apply.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		3.0	3.3	3.6	V
I _{CC}	supply current		-	116	130	mA
PLL						
f _{o(RF)}	RF output frequency	In locked state	14.62	-	15.00	GHz
V _{O(reg)VCO}	VCO regulator output voltage		2.5	2.7	2.9	V
I _{cp}	charge pump current		-	2	-	mA
Ko	VCO steepness		-	0.75	-	GHz/V
$I_{cp} \times K_O$	charge pump current and VCO steepness product		8.0	1.5	2.4	mA·GHz/V

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 Table 10.
 Characteristics ...continued

 $3.0 < V_{CC} < 3.6 V$; Operating conditions of <u>Table 8</u> apply.

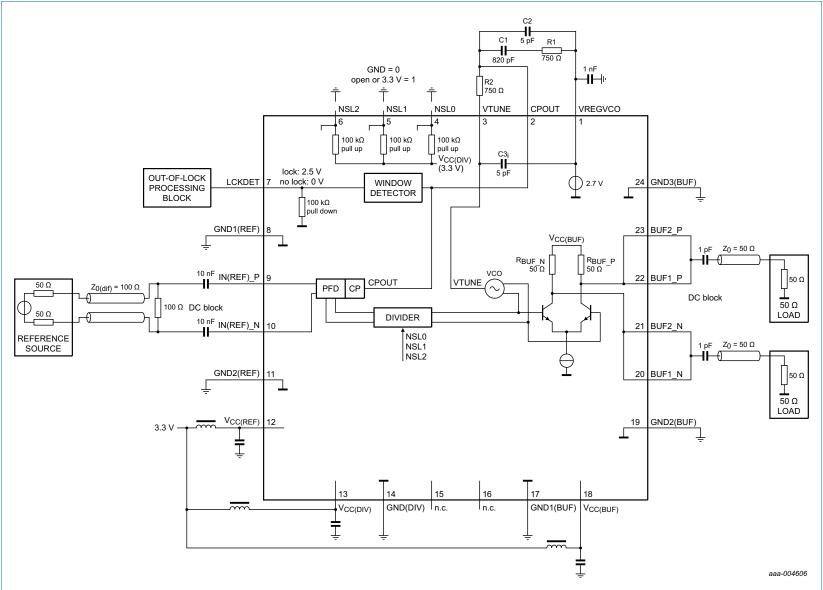
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
φn(VCO)	VCO phase noise	at 1MHz offset		-117	-109	-101	dBc/Hz
Ψn(synth)	synthesizer phase noise	divider value = 64 with loop bandwidth = 2 MHz; reference phase noise = -150 dBc/Hz					
		at 30 kHz offset		-	-108	-103	dBc/Hz
		at 100 kHz offset		-	-109	-104	dBc/Hz
		at 1 MHz offset		-	-109	-104	dBc/Hz
Output bu	ffer						
Po	output power	measured single ended	[1]	-4	-2	0	dBm
RL _{out}	output return loss	measured at demo board and de-embedded to footprint		-	-10	-	dB
$\alpha_{sup(sp)}$	spurious suppression	within \pm 1 MHz		-	-	-60	dBc
$\alpha_{\text{sup(sp)ref}}$	reference spurious suppression	measured at divider value = 64	[2]	-	-	-60	dBc
$\alpha_{H(LO)}$	LO harmonic rejection			-	-10	-	dBc
Lock dete	ctor						
V_{OL}	LOW-level output voltage	$I_{O} = 100 \ \mu A$		-	-	0.4	V
V_{OH}	HIGH-level output voltage	$I_{O} = -100 \mu A$		2.2	-	-	V
R _{pd}	pull-down resistance			70	100	130	kΩ
Divider se	tting (NSL0, NSL1, NSL2)						
R _{pu}	pull-up resistance			70	100	130	kΩ
V_{IL}	LOW-level input voltage			-	-	8.0	V
V _{IH}	HIGH-level input voltage			2.0	-	-	V

^[1] Output stage is a differential pair with 50 Ω collector impedances. Output power is measured per output pin for the fundamental tone only. Output is DC coupled and is AC coupled in on-board.

^[2] Loop filter components dimensioned to achieve a –1 dB PLL loop bandwidth (B_{PLL(loop)}) of 2 MHz under worst case conditions (minimum K_O gain, minimum I_{cp} and maximum value of loop filter components).

Loop filter components spread of 10 % taken into account.

Application information



Application diagram with differential source for IN(REF) and both outputs driving a load, loop filter is type 3

Product data sheet

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Product data sheet

Low phase noise LO generator for VSAT applications

15. Package outline

HVQFN24: plastic thermal enhanced very thin quad flat package; no leads; 24 terminals; body $4 \times 4 \times 0.85$ mm

SOT616-1

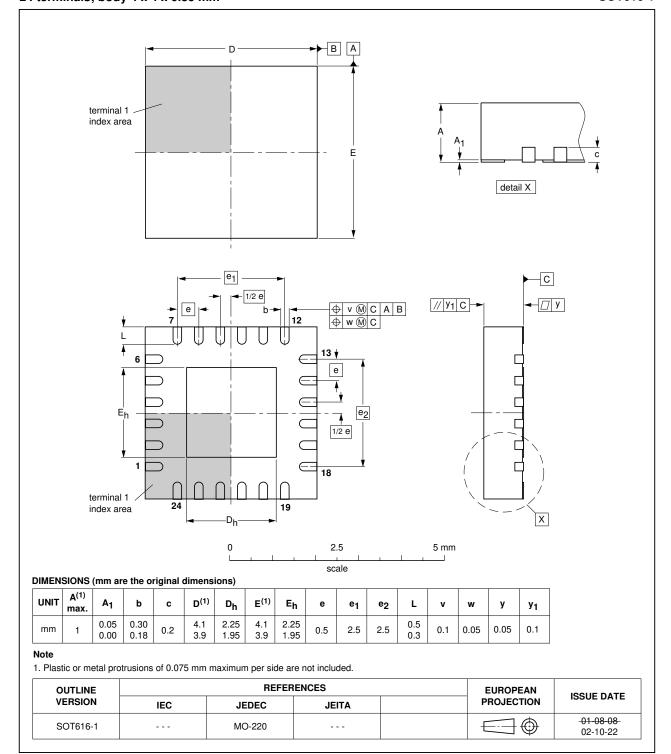


Fig 9. Package outline SOT616-1 (HVQFN24)

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Low phase noise LO generator for VSAT applications

16. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
СР	Charge Pump
K _a band	K-above band
LSB	Least Significant Bit
MSB	Most Significant Bit
PFD	Phase Frequency Detector
PLL	Phase-Locked Loop
VCO	Voltage Controlled Oscillator
VSAT	Very Small Aperture Terminal

17. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
TFF1007HN v.1	20120823	Product data sheet	-	-

Low phase noise LO generator for VSAT applications

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18.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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